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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Application of:)
Kozo Nakamura, et al.)
Serial No.: 09/856,212)
Filed: May 18, 2001)
For: PRODUCTION METHOD FOR SILICON)
SINGLE CRYSTAL AND PRODUCTION)
DEVICE FOR SINGLE CRYSTAL INGOT,)
AND HEAT TREATING METHOD FOR)
SILICON SINGLE CRYSTAL WATER)

Attorney Docket:
1110/82821

Group Art Unit:
1765

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AMENDMENT

Commissioner for Patents
"Attention: Box Amendment"
Washington, D.C. 20231

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SEP 09 2002
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Dear Sir:

The Office Action of May 28, 2002 has been carefully reviewed and the following
Amendments and Remarks are in response thereto.

IN THE CLAIMS

Please cancel claims 6, 8 and 14-23. Please amend claim 7 and 9-11 as set forth
below:

7. (Amended) A Czochralski method-based silicon single crystal production
device, comprising, in a closed container, a crucible element which stores silicon melt,
rotates and is vertically driven, a pulling element for pulling a silicon crystal ingot, while
rotating, from said silicon melt, a heating element for heating said crucible, and a heat
shielding element for shielding radiating heat from said heating element,

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